

Dhananjaya Tripathy, M.Tech.

Designation: Asst. Professor

Department: Department of Electronics and Instrumentation

(JOINED THE INSTITUTE IN 2014)

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RESEARCH INTERESTS

✓ VLSI Design

✓ SemiconductorDevice

Academic Qualifications

M. Tech In VLSI Signal Processing, VSSUT, Odisha.

B.Tech in AppliedElectronics & Instrumentation Engg, CVRCE, Odisha.

Teaching Experience/Industrial Experience/Research Experience

✓ Teaching & Research experience - 10years

PUBLICATIONS

JOURNAL& CONFERENCES:

JOURNALS:

[1].D.Nayak, P. K. Rout, S. S, D. P. Acharya, U. Nanda and **D.Tripathy**, "A novel indirect read technique based SRAM with ability to charge recycle and differential read for low power consumption, high stability and performance ", in Proc. of **Microelectronics** Journal (2020).

CONFERENCES:

[1]. **D.Tripathy**, S.S.Rout, K.Sethi, "A low power noise cancelling LNA for UWB receiver frontend", in Proc. of **IEEE** Power, Communication and Information Technolgy Conference(PCITC), pp.442-446, Sept. 2015, Odisha, India [2]. **D.Tripathy**, T.Manasneha, V.Das, "A single ended TG based 8T SRAM with increased stability and less delay", in Proc. of **IEEE** Recent Trends in Electronics, Information and Communication Technology (RTEICT), pp.1282-1285, May-2017, Bangaluru, India

- [3]. **D.Tripathy**, P.Bhadra, "A High Speed Two Stage Operational Amplifier with High CMRR", in Proc. of **IEEE**Recent Trends in Electronics, Information and Communication Technology (RTEICT), May-2018, Bangaluru, India
- [4]. **D.Tripathy**, D. Nayak, S. M. Biswal , S.K. Swain, B.Baral and S.K.Das" A Low Power LNA using Current Reused Technique for UWB Application", in Proc. of *IEEE* Devices for Integrated Circuits(DevIC), Mar-2019, kolkata,India.
- [5]. D. Nayak, U. Nanda, P.K. Rout, **D.Tripathy**, S.M. Biswal, S.K. Swain, B. Baral and S.K. Das," A Novel Driver less SRAM with Indirect Read for Low Energy Consumption and Read Noise Elimination", in Proc. of *IEEE* Devices for *Integrated Circuits(DevIC)*, Mar-2019, kolkata,India.
- [6]. B. Baral , S.M. Biswal, S.K. Swain, D. Nayak, S.K. Das, and **D.Tripathy**, "RF/Analog&Linearity performance analysis of a downscaled JL DG MOSFET on GaAs substrate for Analog/mixed signal SOC applications", in Proc. of *IEEE Devices for Integrated Circuits(DevIC)*, Mar-2019, kolkata,India.
- [7]. S.K. Swain, S.K. Das, S.M. Biswal, S. Adak, U. Nanda, A. A. Sahoo, D. Nayak, B.Baral and **D.Tripathy**, "Effect of High-K Spacer on the Performance of Non-Uniformly doped DG-MOSFET", in Proc. of *IEEE* Devices for Integrated Circuits (DevIC), Mar-2019, kolkata, India.
- [8]. S.K. Das, S. K. Swain, S.M. Biswal, D. Nayak, U. Nanda, B. Baral and **D.Tripathy**, "Effect of High-K Spacer on the Performance of Gate-Stack Uniformly doped DG-MOSFET", in Proc. of *IEEE* Devices for Integrated Circuits(DevIC), Mar-2019, kolkata,India.
- [9]. S.M. Biswal, S.K. Swain, B. Baral, D. Nayak, U. Nanda, S.K. Das and **D.Tripathy**, "Performance Analysis of Staggeredheterojunctionbased SRG TFET biosensor for health IoT application", in Proc. of *IEEE* Devices for *Integrated Circuits(DevIC)*, Mar-2019, kolkata,India.
- [10]. S. Sarangi, **D. Tripathy**, S.S. Mahapatra, and S.Rout" A Power and Area Efficient CMOS Bandgap Reference Circuiwith an integrated Voltage Reference Branch", in Proc. of **Springer** Modelling ,Simulation, Intelligent Computing (MoSICom-2020), BITS-PilaniDubai Campus.
- [11]. **D. Tripathy**, P.K. Rout, D. Nayak, S. M. Biswal, N. Singh" The impact of oxide layer width variation on the performance parmeters of FinFET", in Proc. of *IEEE*Devices for *Integrated Circuits(DevIC)*, May-2021, kolkata, India.
- [12]. **D. Tripathy**, D.P. Acharya, P.K. Rout and D. Nayak" The impact of GATEthickness variation on FinFET performance parmeters", in Proc. of *IEEE* OITS International Conference on Information Technology(OCIT), Dec-2021, Odisha,India.

ANY OTHER

BookChapter:

[1]. S.S.Rout, **D.Tripathy**, K.Sethi, "An improved bulk injection cascode mixer for receiver frontend" in National Conference on Device and circuits (IEEE), pp. 37-41, Feb. 2016, Odisha,India



Projects:

[1]. Design and fabrication of a low power area optimized band gap reference circuit in XFAB technology for IoT application.